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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/668,873	09/23/2003	Guillaume Guzman	SP02-152 2607		
22928 7	7590 08/13/2004		EXAMINER		
CORNING INCORPORATED			DICKEY, THOMAS L		
SP-TI-3-1 CORNING, NY 14831			ART UNIT	PAPER NUMBER	
			2826		
			DATE MAILED: 08/13/2004	4	

Please find below and/or attached an Office communication concerning this application or proceeding.

					A			
		Application N	o. Applic	cant(s)				
Office Action Summary		10/668,873	GUZM	IAN ET AL.				
		Examiner	Art Ur	nit				
		Thomas L Dick						
The Period for Rep	MAILING DATE of this communic bly	ation appears on the co	er sheet with the correspo	ondence address				
THE MAILII - Extensions of after SIX (6) I - If the period f - If NO period f - Failure to rep Any reply rec	NED STATUTORY PERIOD FO NG DATE OF THIS COMMUNIC firme may be available under the provisions of MONTHS from the mailing date of this communion reply specified above is less than thirty (30) for reply is specified above, the maximum statuly within the set or extended period for reply we leved by the Office later than three months after them adjustment. See 37 CFR 1.704(b).	ATION. 37 CFR 1.136(a). In no event, he nication. days, a reply within the statutory etory period will apply and will expill, by statute, cause the application.	owever, may a reply be timely filed ninimum of thirty (30) days will be co re SIX (6) MONTHS from the mailin n to become ABANDONED (35 U.S	onsidered timely. g date of this communication. S.C. § 133).				
Status								
2a)∐ This a 3)∐ Since	 Responsive to communication(s) filed on <u>28 June 2004</u>. This action is FINAL. 2b) This action is non-final. Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i>, 1935 C.D. 11, 453 O.G. 213. 							
Disposition of	Claims							
4a) 0: 5)	 ✓ Claim(s) 1-19 is/are pending in the application. ✓ 4a) Of the above claim(s) 15-18 is/are withdrawn from consideration. ✓ Claim(s) is/are allowed. ✓ Claim(s) 1-14 is/are rejected. ✓ Claim(s) 19 is/are objected to. ✓ Claim(s) are subject to restriction and/or election requirement. 							
Application Pa	pers							
10)⊠ The di Applio Repla	pecification is objected to by the rawing(s) filed on 23 September ant may not request that any objecticement drawing sheet(s) including the ath or declaration is objected to be	2003 is/are: a)⊠ acce on to the drawing(s) be he ne correction is required if	ld in abeyance. See 37 CFI the drawing(s) is objected to	R 1.85(a). o. See 37 CFR 1.121(d)).			
Priority under	35 U.S.C. § 119							
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.								
2) Notice of Dra 3) Information [ferences Cited (PTO-892) Iftsperson's Patent Drawing Review (PTO Disclosure Statement(s) (PTO-1449 or P [*] Mail Date <u>09/23/2003</u> .	D-948) FO/SB/08) 5) [Interview Summary (PTO-41 Paper No(s)/Mail Date. Notice of Informal Patent App Other:	_•				

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DETAILED ACTION

1. The amendment filed on 06/28/2004 has been entered. Applicant should note that

there is a disagreement between Applicant's remarks and Applicant's "clean copy" of

claims. Applicant remarks that he intends to cancel claims 15-18 but in the "clean copy"

Applicant withdraws the same. As a result, the "clean copy" takes precedent and claims

15-18 are withdrawn but not cancelled.

Election/Restriction

2. Applicant's election without traverse of Group II, claims 1-14 and 19, in the Paper

filed 06/28/2004 is acknowledged.

Oath/Declaration

3. The oath/declaration filed on 03/08/2004 is acceptable.

Drawings

4. The formal drawings filed on 09/23/2003 are acceptable.

Priority

5. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which

papers have been placed of record in the file.

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Information Disclosure Statement

6. The Information Disclosure Statement filed on 09/23/2003 has been considered.

Claim Rejections - 35 USC § 102

7. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

A. Claims 1-9 and 11-14 are rejected under 35 U.S.C. 102(b) as being anticipated by OHTAKA et al. (5,108,843).

Ohtaka et al. discloses a thin film transistor (TFT) suitable for applications selected from the group consisting of liquid crystal displays (LCDs) and light emitting diodes (LEDs) comprising a glass, glass-ceramic, or ceramic substrate 201 suitable for use in electronic and integrated circuits; a layer of refractory polycrystalline material 202 formed on at least a portion of the substrate 201; and a layer of polycrystalline silicon 203 formed on the refractory layer. With regard to claims 4-7,13, and 14, Ohtaka et al. discloses that the refractory material 202 may be CVD deposited polycrystalline zirconia (ZrO₂) an oxide characterized by having low thermal conductivity and high electrical permittivity, having at least one crystal parameter (lattice constant, as applicant admits at paragraph 0045 of the instant application) close to that of crystalline silicon, and

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comprising an element (Zr) selected from the group consisting of AI, Mg, Ti, Zr, Y, Ca, Mo, Ce, Hf, Ta, B, V and a combination of these. With regard to claims 8 and 9, Ohtaka et al. discloses that the refractory material 202 may be TiC, SiC, Si₃N₄ or BN, and thus a carbide, nitride or boride containing Si. Note figure 1 and column 4 lines 3-5, 12-23, and 34-36 of Ohtaka et al.

The applicant's claims 11 and 13 do not distinguish over the Ohtaka et al. reference regardless of the process used to form the refractory material, because only the final product is relevant, not the recited processes of sol-gel technique or anodic oxidation, electron, ion, atom or laser beam processes.

Note that a "product by process" claim is directed to the product per se, no matter how actually made. In re Hirao, 190 USPQ 15 at 17 (footnote 3). See also In re Brown, 173 USPQ 685; In re Luck, 177 USPQ 523; In re Fessmann, 180 USPQ 324; In re Avery, 186 USPQ 161; In re Wertheim, 191 USPQ 90 (209 USPQ 554 does not deal with this issue); and In re Marosi et al., 218 USPQ 289, all of which make it clear that it is the patentability of the final product per se which must be determined in a "product by process" claim and not the patentability of the process, and that an old or obvious product produced by a new method is not patentable as a product, whether claimed in "product by process" claims or not. Note that applicant has the burden of proof in such cases, as the above caselaw makes clear. See also MPEP 706.03(e).

B. Claims 1-7 and 10-14 are rejected under 35 U.S.C. 102(b) as being anticipated by FORK et al. (5,733,641).

Fork et al. discloses a thin film transistor (TFT) suitable for applications selected from the group consisting of liquid crystal displays (LCDs) and light emitting diodes (LEDs) comprising a glass, glass-ceramic, or ceramic substrate 100 suitable for use in electronic and integrated circuits; a porous layer of CVD or sol-gel deposited refractory polycrystalline material 102 formed on at least a portion of the substrate 100; and a layer of polycrystalline silicon 108 formed on the refractory layer, wherein the refractory material 102 may comprise Mg, Al, and Zr, which are selected from the group consisting of Al, Mg, Ti, Zr, Y, Ca, Mo, Ce, Hf, Ta, B, V and a combination of these. With regard to claims 5-7, and 14, Ohtaka et al. discloses that the refractory material 102 may be polycrystalline zirconia (ZrO₂) an oxide characterized by having low thermal conductivity and high electrical permittivity, having at least one crystal parameter (lattice constant, as applicant admits at paragraph 0045 of the instant application) close to that of crystalline silicon. Note figures 1, 2A-2E, and column 2 lines 6-16 and column 4 lines 8-44 of Fork et al.

The applicant's claim 13 does not distinguish over the Fork et al. reference regardless of the process used to form the refractory material, because only the final product is relevant, not the recited processes of electron, ion, atom or laser beam processes.

Note that a "product by process" claim is directed to the product per se, no matter how actually made. In re Hirao, 190 USPQ 15 at 17 (footnote 3). See also In re Brown, 173 USPQ 685; In re Luck, 177 USPQ 523; In re Fessmann, 180 USPQ 324; In re

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Avery, 186 USPQ 161; In re Wertheim, 191 USPQ 90 (209 USPQ 554 does not deal with this issue); and In re Marosi et al., 218 USPQ 289, all of which make it clear that it is the patentability of the final product per se which must be determined in a "product by process" claim and not the patentability of the process, and that an old or obvious product produced by a new method is not patentable as a product, whether claimed in "product by process" claims or not. Note that applicant has the burden of proof in such cases, as the above caselaw makes clear. See also MPEP 706.03(e).

Allowable Subject Matter

8. Claim 19 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Conclusion

9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thomas L Dickey whose telephone number is 571-272-1913. The examiner can normally be reached on Monday-Thursday 8-6.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan J Flynn can be reached on 571-272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

TLD 07/04

Minhloan Tran
Primary Examiner
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